LASER DIODE
SPECIFICATIONS FOR APPROVAL

Customer :

Model : QL90F7S-A/B/C

Signature of Approval

Approved by

Checked by

Issued by

Approval by Customer
QL90F7S-A/B/C

InGaAs Laser Diode

♦ OVERVIEW

QL90F7S-A/B/C is a MOCVD grown 905nm band InGaAs laser diode with quantum well structure. It’s an attractive light source, with a typical light output power of 10mW for Laser, industrial optical module and sensor application.

♦ APPLICATION

- Sensor

♦ FEATURES

- Visible Light Output : $\lambda_p = 905$ nm
- Optical Power Output : 10mW CW
- Package Type : TO-18 (5.6mmφ)
- Built-in Photo Diode for Monitoring Laser Diode

♦ ELECTRICAL CONNECTION

<table>
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<tr>
<th>Bottom View</th>
<th>Pin Configuration</th>
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<td>A</td>
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<td>LD cathode, PD anode (Fig. 1)</td>
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<td>B</td>
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<td>LD , PD anode (Fig. 2)</td>
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<td>C</td>
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<td>LD anode, PD cathode (Fig. 3)</td>
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Fig. 1 QL90F7SA  
Fig. 2 QL90F7SB  
Fig. 3 QL90F7SC
The above product specifications are subject to change without notice.